N-Channel Silicon MOSFET



2SK3448

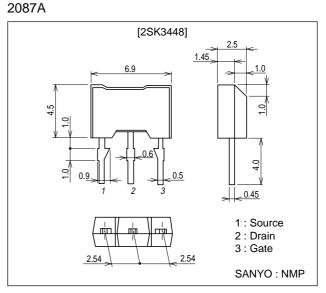
Ultrahigh-Speed Switching Use

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.
- · Meets radial taping.

Package Dimensions

unit : mm



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		60	V
Gate-to-Source Voltage	VGSS		±20	V
Drain Current (DC)	۱ _D		2.5	A
Drain Current (Pulse)	IDP	PW≤10µs, duty cycle≤1%	10	A
Allowable Power Dissipation	PD		1	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Symbol	Conditions	Ratings			Linit
		min	typ	max	Unit
V(BR)DSS	ID=1mA, VGS=0	60			V
IDSS	V _{DS} =60V, V _{GS} =0			10	μA
IGSS	V _{GS} =±16V, V _{DS} =0			±10	μA
VGS(off)	V _{DS} =10V, I _D =1mA	1.0		2.4	V
yfs	V _{DS} =10V, I _D =1.5A	2.7	3.8		S
R _{DS} (on)1	ID=1.5A, VGS=10V		115	150	mΩ
R _{DS} (on)2	I _D =1.0A, V _{GS} =4V		150	210	mΩ
	V(BR)DSS IDSS IGSS VGS(off) yfs RDS(on)1	V(BR)DSS ID=1mA, VGS=0 IDSS VDS=60V, VGS=0 IGSS VGS=±16V, VDS=0 VGS(off) VDS=10V, ID=1mA yfs VDS=10V, ID=1.5A RDS(on)1 ID=1.5A, VGS=10V	With With With With With With With With	Symbol Conditions min typ V(BR)DSS ID=1mA, VGS=0 60 60 IDSS VDS=60V, VGS=0 60 60 IGSS VGS=±16V, VDS=0 60 60 VGS(off) VDS=10V, ID=1mA 1.0 60 Iyfs VDS=10V, ID=1.5A 2.7 3.8 RDS(on)1 ID=1.5A, VGS=10V 115 115	Symbol Conditions min typ max V(BR)DSS ID=1mA, VGS=0 60 60 10 IDSS VDS=60V, VGS=0 60 10 10 IGSS VGS=±16V, VDS=0 ±10 ±10 VGS(off) VDS=10V, ID=1mA 1.0 2.4 Jyfs VDS=10V, ID=1.5A 2.7 3.8 RDS(on)1 ID=1.5A, VGS=10V 115 150

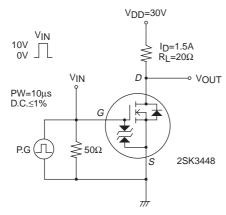
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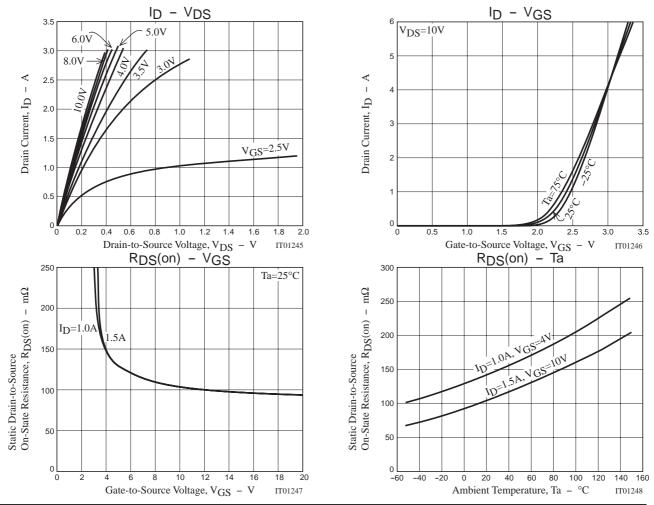
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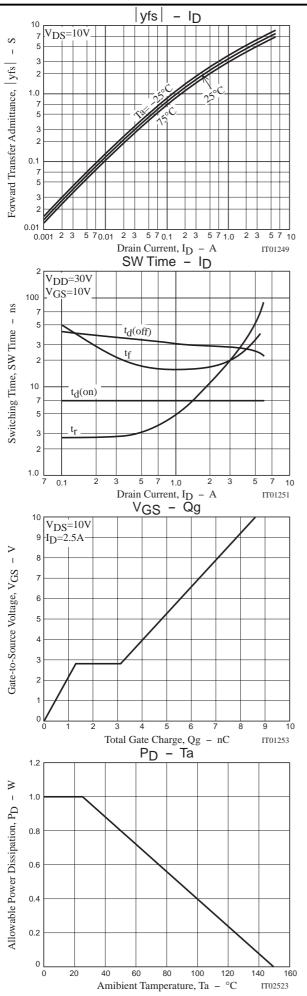
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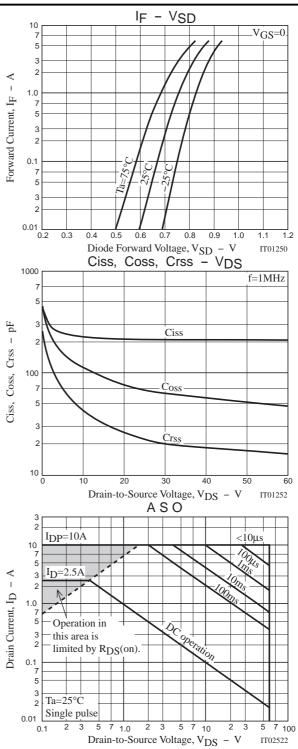
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		220		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		75		pF
Reverse Transfer Capacitance	Crss	VDS=20V, f=1MHz		25		pF
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		7		ns
Rise Time	tr	See specified Test Circuit		8		ns
Turn-OFF Delay Time	td(off)	See specified Test Circuit		28		ns
Fall Time	tf	See specified Test Circuit		16		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =2.5A		8.6		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =2.5A		1.3		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =2.5A		1.8		nC
Diode Forward Voltage	V _{SD}	I _S =2.5A, V _{GS} =0		0.83	1.2	V

Switching Time Test Circuit









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